

PROCESS FOR MONITORING THE GASEOUS
ENVIRONMENT OF A CRYSTAL PULLER
FOR SEMICONDUCTOR GROWTH

ABSTRACT OF THE INVENTION

5 This invention relates to a process for monitoring the
gaseous environment within a sealed crystal pulling furnace,
used for the growth of an ingot of a semiconductor material
in a growth chamber maintained at a sub-atmospheric
pressure. The process comprises sealing the chamber,
10 reducing the pressure within the sealed chamber to a sub-
atmospheric level, introducing a process gas into the
chamber to purge the chamber and form a gaseous environment
therein, and analyzing the gaseous environment within the
chamber for the presence of a contaminant gas in a
15 concentration which is greater than the concentration of the
contaminant gas in the process gas.